TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74HC133AP,TC74HC133AF

13-Input NAND Gate

The TC74HC133A is a high speed CMOS 13-INPUT NAND GATE fabricated with silicon gate C²MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

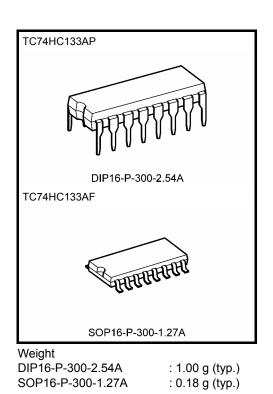
The internal circuit is composes of 7 stages, including a buffer output, which provide high noise immunity and stable output.

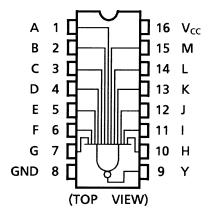
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

Features

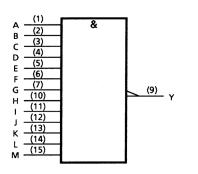
- High speed: $t_{pd} = 13$ ns (typ.) at VCC = 5 V
- Low power dissipation: $I_{CC} = 1 \ \mu A \ (max)$ at $Ta = 25^{\circ}C$
- High noise immunity: $V_{\text{NIH}} = V_{\text{NIL}} = 28\% V_{\text{CC}}$ (min)
- Output drive capability: 10 LSTTL loads
- Symmetrical output impedance: |IOH| = IOL = 4 mA (min)
- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Wide operating voltage range: V_{CC} (opr) = 2 to 6 V
- Pin and function compatible with 74LS133

Pin Assignment





IEC Logic Symbol



Truth Table

Input	Output
All Inputs High	L
All Other Combinations	Н

Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit	
Supply voltage range	V _{CC}	–0.5 to 7	V	
DC input voltage	V _{IN}	–0.5 to V _{CC} + 0.5	V	
DC output voltage	V _{OUT}	–0.5 to V _{CC} + 0.5	V	
Input diode current	IIK	±20	mA	
Output diode current IOK		±20	mA	
DC output current	IOUT	±25	mA	
DC V _{CC} /ground current	ICC	±50	mA	
Power dissipation	PD	500 (DIP) (Note 2)/180 (SOP)	mW	
Storage temperature	T _{stg}	–65 to 150	°C	

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = -40 to 65° C. From Ta = 65 to 85° C a derating factor of -10 mW/°C shall be applied until 300 mW.

Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	Supply voltage V _{CC} 2 to 6		V
Input voltage VIN		0 to V _{CC}	V
Output voltage	V _{OUT}	0 to V _{CC}	V
Operating temperature	T _{opr}	-40 to 85	°C
		0 to 1000 (V _{CC} = 2.0 V)	
Input rise and fall time	t _r , t _f	0 to 500 ($V_{CC} = 4.5 \text{ V}$)	ns
		0 to 400 ($V_{CC} = 6.0 \text{ V}$)	

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Electrical Characteristics

DC Characteristics

Characteristics Symbol			Test Condition		Ta = 25°C			Ta = -40 to 85°C		Unit
		,		$V_{CC}(V)$	Min	Тур.	Max	Min	Max	
				2.0	1.50	_	_	1.50	_	
High-level input voltage	VIH	—		4.5	3.15	—	—	3.15	—	V
Ŭ				6.0	4.20	_	_	4.20	—	
				2.0			0.50	—	0.50	
Low-level input voltage	VIL	—		4.5	_	—	1.35	—	1.35	V
Ŭ				6.0		_	1.80		1.80	
	V _{OH}	V _{IN} = V _{IH} or V _{IL}		2.0	1.9	2.0	—	1.9	—	
			$I_{OH} = -20 \ \mu A$	4.5	4.4	4.5	—	4.4	—	
High-level output voltage				6.0	5.9	6.0	_	5.9		V
			I _{OH} = -4 mA	4.5	4.18	4.31	—	4.13	—	
			$I_{OH} = -5.2 \text{ mA}$	6.0	5.68	5.80	_	5.63		
		V _{IN} = V _{IH} or V _{IL}		2.0	_	0.0	0.1	—	0.1	
			$I_{OL} = 20 \ \mu A$	4.5	_	0.0	0.1	—	0.1	
Low-level output voltage	V _{OL}			6.0		0.0	0.1		0.1	V
			$I_{OL} = 4 \text{ mA}$	4.5	—	0.17	0.26	—	0.33	
			$I_{OL} = 5.2 \text{ mA}$	6.0	_	0.18	0.26	_	0.33	
Input leakage current	I _{IN}	V _{IN} = V _{CC} or GND		6.0			±0.1		±1.0	μΑ
Quiescent supply current	ICC	$V_{IN} = V_{CC}$ or GND		6.0			1.0	_	10.0	μΑ

AC Characteristics ($C_L = 15 \text{ pF}$, $V_{CC} = 5 \text{ V}$, $Ta = 25^{\circ}C$, input: $t_r = t_f = 6 \text{ ns}$)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Output transition time	t _{TLH}	—		4	8	ns
	t _{THL}					115
Propagation delay time	t _{pLH}			13	22	ns
	t _{pHL}			15	22	113

AC Characteristics ($C_L = 50 \text{ pF}$, input: $t_r = t_f = 6 \text{ ns}$)

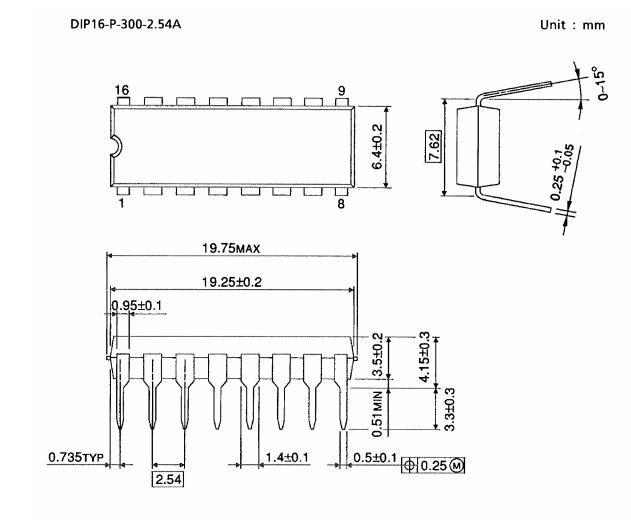
Characteristics	Symbol			Ta = 25°C			Ta = -40 to 85°C		Unit
	,		$V_{CC}(V)$	Min	Тур.	Max	Min	Max	
	t		2.0	_	25	75	_	95	
Output transition time	t _{TLH}	—	4.5	—	7	15	—	19	ns
	t _{THL}		6.0	—	6	13	—	16	
timo			2.0	_	42	130		165	
	t _{pLH}	_	4.5	—	16	26	—	33	ns
	t _{pHL}		6.0	—	14	22	—	28	
Input capacitance	C _{IN}	_		_	5	10	_	10	pF
Power dissipation capacitance	C _{PD} (Note)			_	29	_	_	_	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC} (opr) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

Package Dimensions



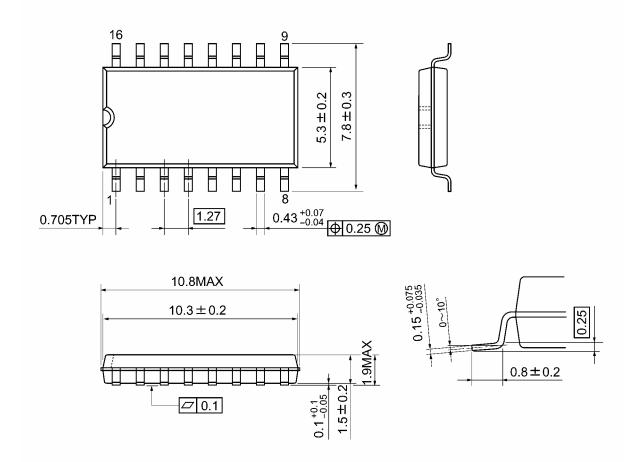
Weight: 1.00 g (typ.)



Package Dimensions

SOP16-P-300-1.27A

Unit: mm



Weight: 0.18 g (typ.)

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20070701-EN GENERAL

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